

SANYO	No.710D	DS-135
		Diffused Junction Type Silicon Diode 1.0A Power Rectifier

Features

- Plastic molded type
- Peak reverse voltage $V_{RM} = -100$ to $-400V$
- Average rectified current $I_O = 1.0A$

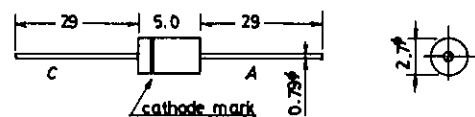
Absolute Maximum Ratings at $T_a = 25^\circ C$

			DS135E	DS135D	DS135C	unit
Peak Reverse Voltage	V_{RM}		-100	-200	-400	V
Average Rectified Current	I_O	$T_a = 60^\circ C$	→	→	1.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1 cycle	→	→	50	A
Junction Temperature	T_j		→	→	150	$^\circ C$
Storage Temperature	T_{stg}		→	→	-40 to +150	$^\circ C$

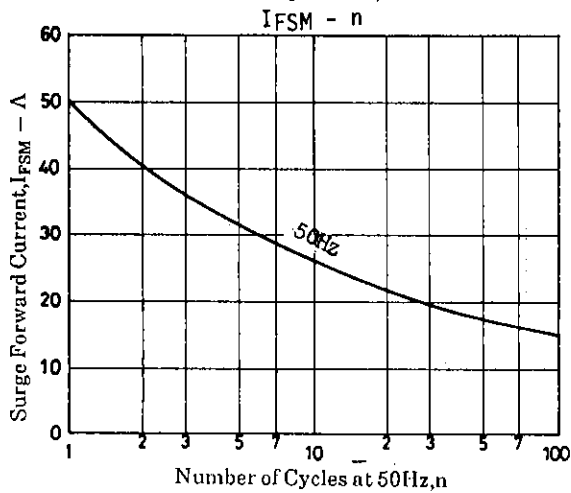
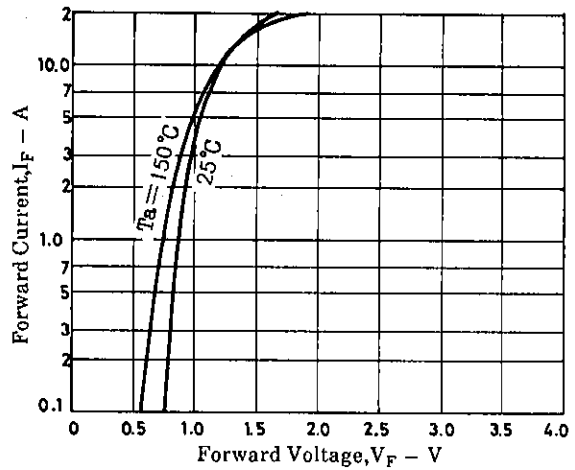
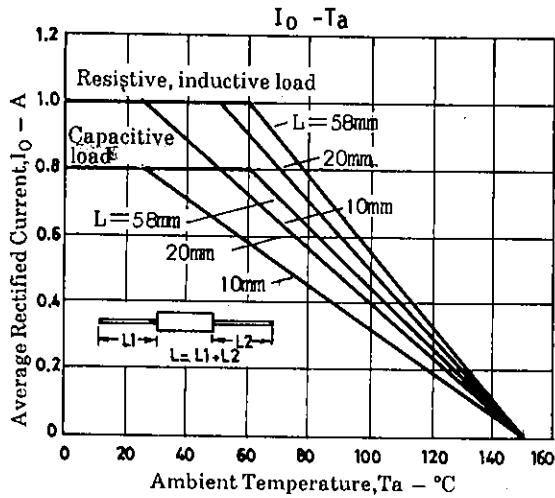
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Forward Voltage	V_F	$I_F = 1.0A$			1.0	V
Reverse Current	I_R	V_R : At each V_{RM}			-10	μA

Package Dimensions 1005
(unit: mm)



C: Cathode
A: Anode



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